WHAT IS CLAIMED IS:

1. A method of forming a laminate, comprising a first step of forming an intermediate layer on a base member, and a second step of forming a metal layer on the intermediate layer, the adhesion of the metal layer to the base member being lower than that of the intermediate layer, the reflectance of the metal layer being higher than that of the intermediate layer, wherein the rate of formation of the metal layer is increased at an intermediate stage in said second step.

2. The method according to claim 1, wherein the intermediate layer is formed to a thickness within the range of 30 nm to 100 nm on the base member.

3. The method according to claim 1, wherein the rate of formation of the metal layer before increasing the formation rate is set within the range of 0.5 nm/s to 4.0 nm/s.

4. The method according to claim 1, wherein the rate of formation of the metal layer is increased at a point in time when the metal layer is formed to a thickness within the range of 1 nm to 100 nm on the intermediate layer.

5. A method of forming a laminate, comprising a first step of forming a metal layer on a base member to be processed, and a second step of forming a metal oxide layer on the metal layer, wherein the rate of formation of the metal layer is reduced at an intermediate stage in said first step, and the rate of formation of the metal oxide layer is increased at an intermediate stage in said second step.

6. The method according to claim 5, wherein the rate of formation of the metal layer is reduced to a value within the range of 0.5 nm/s to 4.0 nm/s.

7. The method according to claim 5, wherein the metal layer is formed to a thickness within the range of 1 nm to 100 nm after the rate of formation of the metal layer has been reduced, and the metal oxide layer is then formed on the metal layer.

8. The method according to claim 5, wherein the rate of formation of the metal oxide layer before increasing the formation rate is set within the range of 0.05 nm/s to 3.0 nm/s.

9. The method according to claim 5, wherein the rate of formation of the metal oxide layer is increased at a point in time when the metal oxide

layer is formed to a thickness within the range of 5 nm to 50 nm on the metal layer.

10. The method according to claim 5, wherein oxygen is contained in the forming atmosphere at least immediately before the completion of formation of the metal layer and immediately after the start of formation of the metal oxide layer.

11. The method according to claim 10, wherein oxygen is contained in the forming atmosphere after reducing the rate of formation of the metal layer and before increasing the rate of formation of the metal oxide layer.

12. A method of manufacturing a photovoltaic device, comprising a first step of forming an intermediate layer on a base member, a second step of forming a metal layer on the intermediate layer, the adhesion of the metal layer to the base member being lower than that of the intermediate layer, the reflectance of the metal layer being higher than that of the intermediate layer, and a third step of forming a semiconductor layer directly on the metal layer or with a metal oxide layer interposed between the semiconductor layer and the metal layer, wherein the rate of formation of the metal layer is increased

at an intermediate stage in said second step.

13. A method of manufacturing a photovoltaic device, comprising a first step of forming a metal layer on a base member to be processed, a second step of forming a metal oxide layer on the metal layer, and a third step of forming a semiconductor layer on the metal oxide layer, wherein the rate of formation of the metal layer is reduced at an intermediate stage in said first step, and the rate of formation of the metal oxide layer is increased at an intermediate stage in said second step.